

Supporting Information

First principles study on the electronic structures and contact properties of graphene/XC (X = P, As, Sb, Bi) van der Waals heterostructures

Xuemin Hu^a, Wenqiang Liu^b, Jialin Yang^b, Shengli Zhang^{*b,c}, Yuanfeng Ye^{*a}

^aSchool of Material Engineering, Jinling Institute of Technology, Nanjing 211169, China

^bMIIT Key Laboratory of Advanced Display Materials and Devices, School of Materials Science and Engineering, Nanjing University of Science and Technology, Nanjing 210094, China

^cNational Laboratory of Solid State Microstructures, Nanjing University, Nanjing 210093, China

Email: zhangslvip@njust.edu.cn, yyf@jit.edu.cn

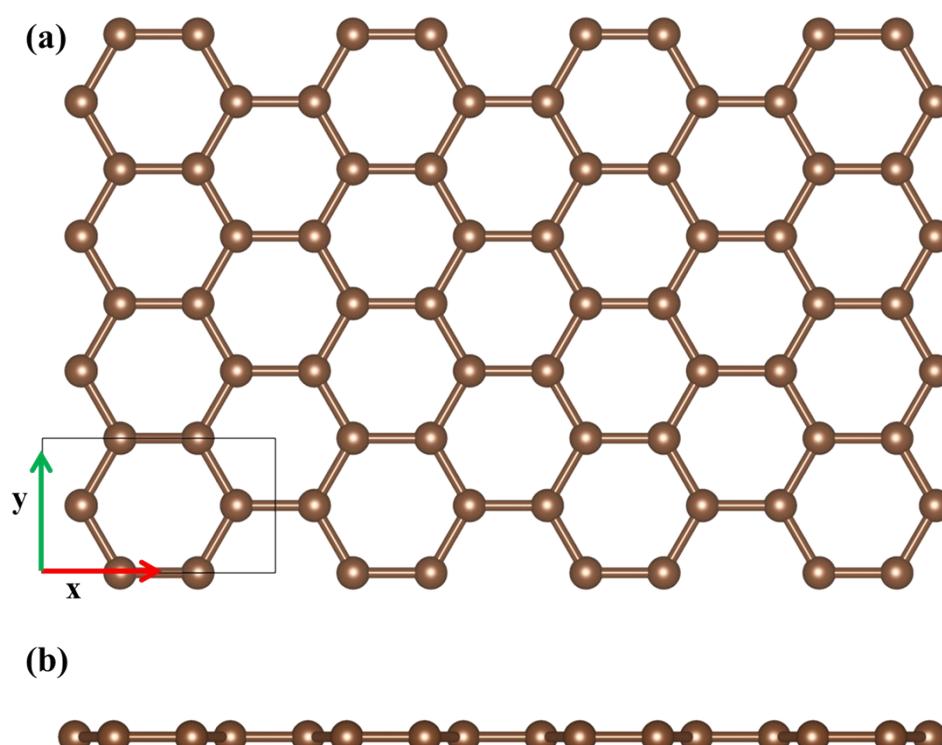


Fig. S1 (a) Top and (b) side views of the optimized graphene (Gr) monolayer.

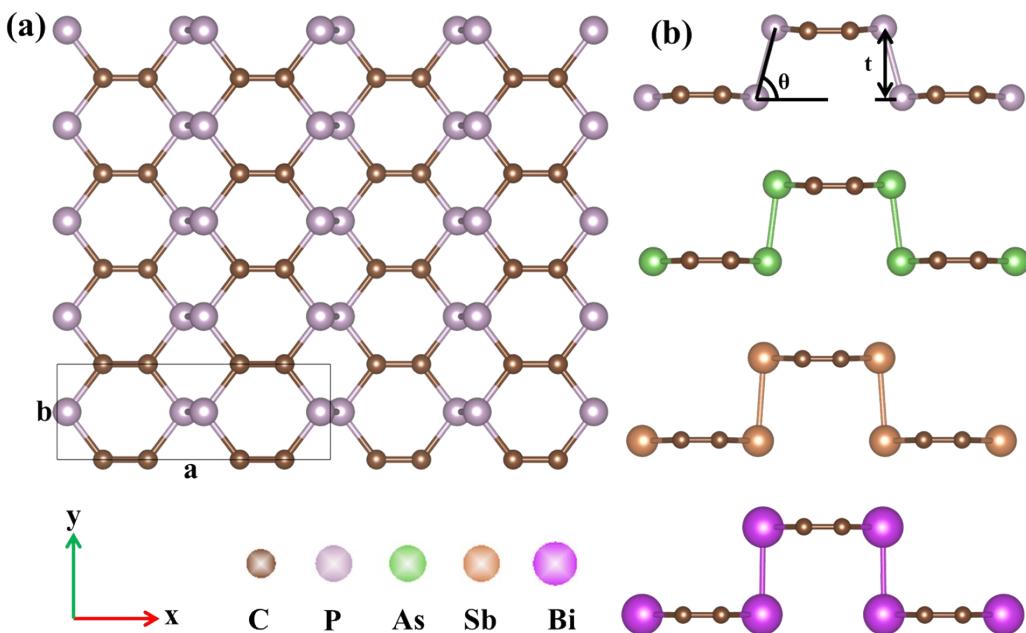


Fig. S2 (a) Top and (b) side views of the optimized atomic structures of XC ($X = P, As, Sb, Bi$) monolayers.

Table S1 Optimized geometric parameters of XC ($X = P, As, Sb, Bi$) monolayers: bonding length (X-C, C-C and X-X), inclination (θ) of X-X bond and vertical distance (t) between two adjacent X atoms.

| | X-C (Å) | C-C (Å) | X-X (Å) | θ (°) | t (Å) |
|-----|---------|---------|---------|--------------|-------|
| PC | 1.82 | 1.36 | 2.35 | 74.94 | 2.27 |
| AsC | 1.98 | 1.35 | 2.57 | 82.64 | 2.54 |
| SbC | 2.20 | 1.34 | 2.92 | 86.02 | 2.91 |
| BiC | 2.32 | 1.33 | 3.06 | 89.28 | 3.05 |

Table S2 Optimized lattice constants of Gr and XC monolayers ($X = P, As, Sb, Bi$).

| Lattice constants | Gr | PC | AsC | SbC | BiC |
|-------------------|------|------|------|------|------|
| a (Å) | 4.27 | 8.56 | 8.19 | 8.50 | 8.47 |
| b (Å) | 2.47 | 2.92 | 3.13 | 3.47 | 3.66 |

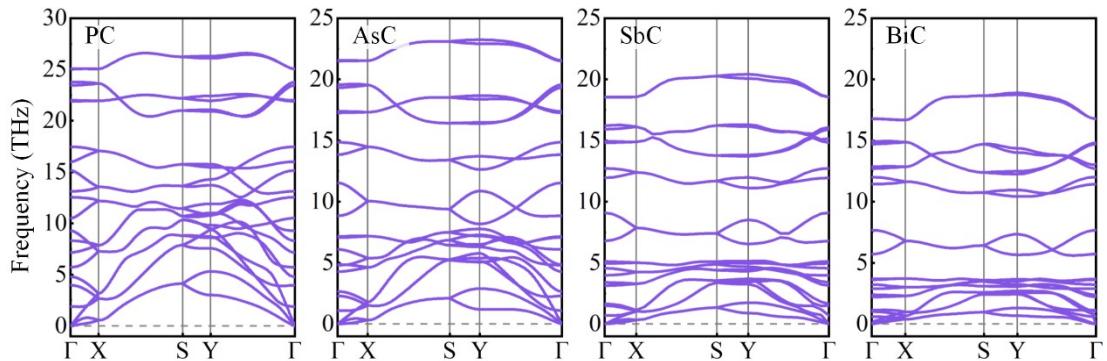


Fig. S3 Phonon spectra of isolated XC monolayers (X = P, As, Sb, Bi).

Table S3 Lattice mismatches of Gr/XC (X = P, As, Sb, Bi) heterostructures.

| Lattice mismatch | Gr/PC | Gr/AsC | Gr/SbC | Gr/BiC |
|------------------|-------|--------|--------|--------|
| x direction | 0.06% | 2.12% | 0.28% | 0.48% |
| y direction | 0.75% | 2.48% | -2.63% | 0.63% |

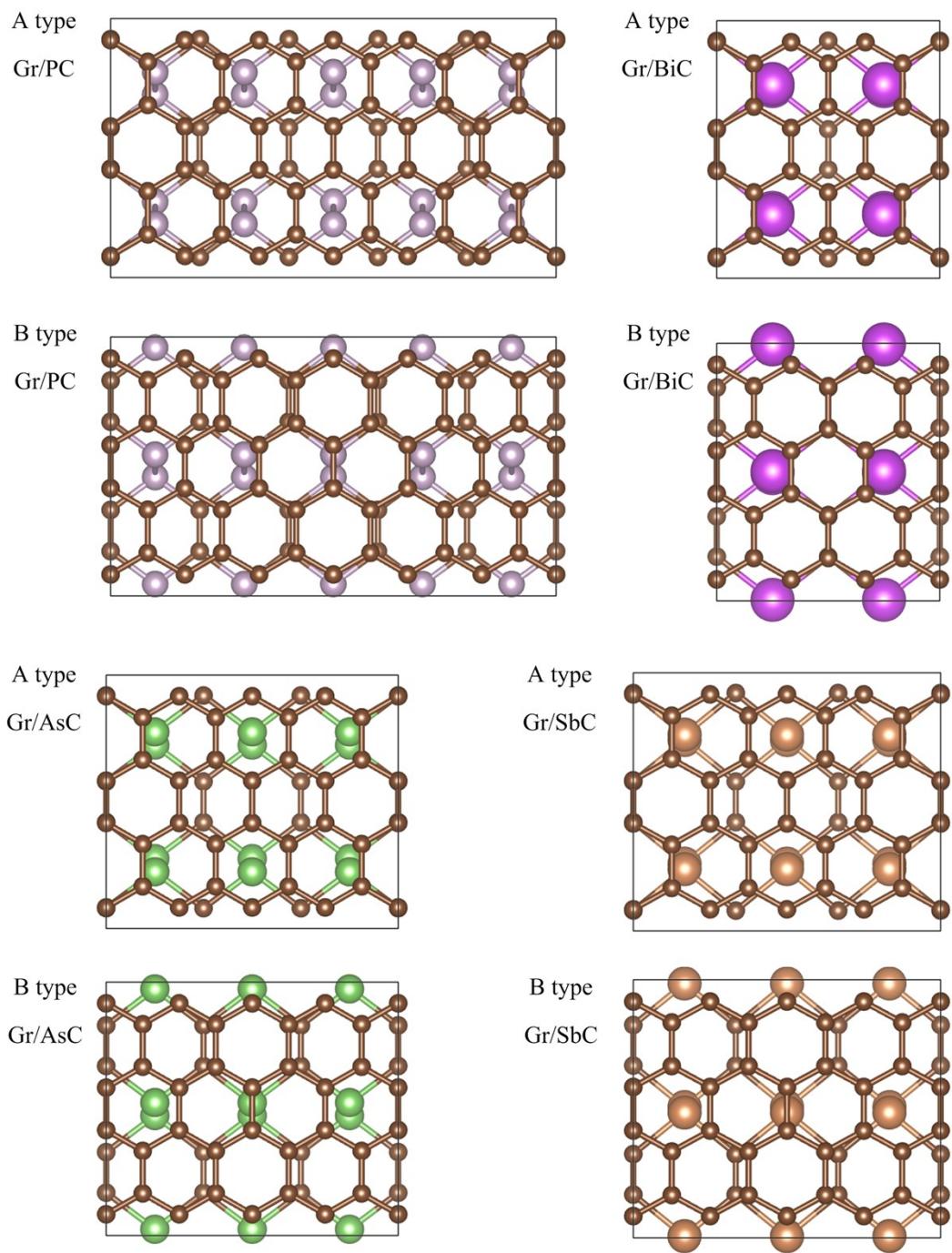


Fig. S4 Geometry configurations for Gr/XC heterostructures (X = P, As, Sb, Bi) with two different stacking types.

Table S4 Total energies (E_{tot}) of Gr/XC heterostructures (X = P, As, Sb, Bi) with different stacking types.

| Gr/XC | type | E_{tot} (eV) |
|--------|------|-----------------------|
| Gr/PC | A | -723.9904 |
| | B | -723.9883 |
| Gr/AsC | A | -449.2705 |
| | B | -446.6225 |
| Gr/SbC | A | -438.4028 |
| | B | -435.3700 |
| Gr/BiC | A | -313.7318 |
| | B | -313.7298 |

Table S5 The bond lengths and bond angles of Gr/XC heterostructures.

| Gr/XC | X-C (Å) | C-C (Å) | X-X (Å) | C-X-X (°) |
|--------|---------|---------|---------|-----------|
| Gr/PC | 1.83 | 1.36 | 2.30 | 97.09 |
| Gr/AsC | 2.01 | 1.35 | 2.54 | 93.48 |
| Gr/SbC | 2.18 | 1.34 | 2.92 | 91.18 |
| Gr/BiC | 2.33 | 1.33 | 3.04 | 90.77 |

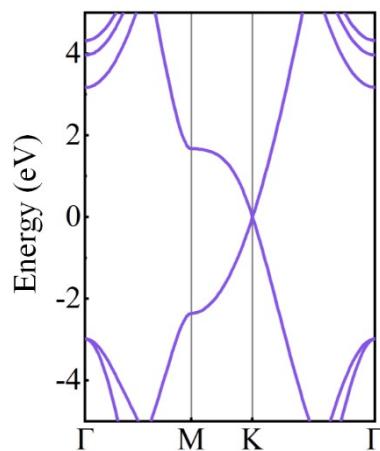


Fig. S5 The band structure of pristine graphene.

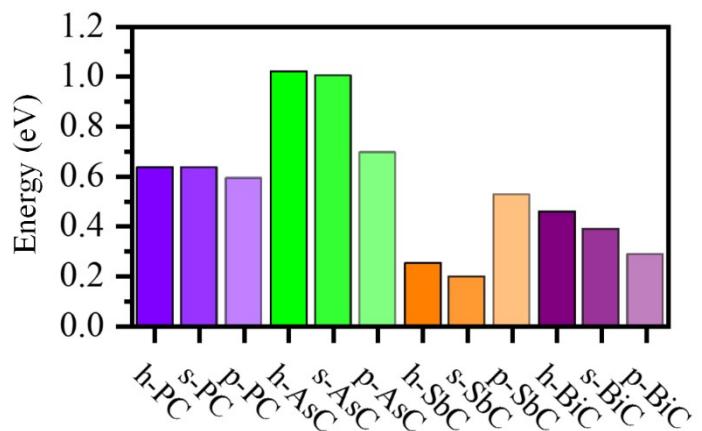


Fig. S6 The comparison of the band gaps of XC in the Gr/XC heterostructures (h-XC), isolated XC with strained supercell sizes of heterostructures (s-XC) and pristine XC without strains (p-XC).